



**Absolute Maximum Ratings – Sensitive SCRs**

Symbol	Parameter	Test Conditions		Value	Unit
$I_{T(RMS)}$	RMS on-state current	Sxx08LSy	$T_c = 80^\circ\text{C}$	8	A
		Sxx08RSy Sxx08DSy Sxx08VSy	$T_c = 95^\circ\text{C}$		
$I_{T(AV)}$	Average on-state current	Sxx08LSy	$T_c = 80^\circ\text{C}$	5.1	A
		Sxx08RSy Sxx08DSy Sxx08VSy	$T_c = 95^\circ\text{C}$		
$I_{TSM}$	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$ ; $T_J$ (initial) = $25^\circ\text{C}$		83	A
		single half cycle; $f = 60\text{Hz}$ ; $T_J$ (initial) = $25^\circ\text{C}$		100	
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3 \text{ ms}$		41	$\text{A}^2\text{s}$
$di/dt$	Critical rate of rise of on-state current	$f = 60 \text{ Hz}; T_J = 110^\circ\text{C}$		70	$\text{A}/\mu\text{s}$
$I_{GTM}$	Peak gate current	$T_J = 110^\circ\text{C}$		1.6	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 110^\circ\text{C}$		0.4	W
$T_{stg}$	Storage temperature range			-40 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range			-40 to 110	$^\circ\text{C}$

Note: xx = voltage, y = sensitivity

**Absolute Maximum Ratings – Standard SCRs**

Symbol	Parameter	Test Conditions		Value	Unit
$I_{T(RMS)}$	RMS on-state current	Sxx08L	$T_c = 100^\circ\text{C}$	8	A
		Sxx08R Sxx08D Sxx08V	$T_c = 110^\circ\text{C}$		
$I_{T(AV)}$	Average on-state current	Sxx08L	$T_c = 100^\circ\text{C}$	5.1	A
		Sxx08R Sxx08D Sxx08V	$T_c = 110^\circ\text{C}$		
$I_{TSM}$	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$ ; $T_J$ (initial) = $25^\circ\text{C}$		83	A
		single half cycle; $f = 60\text{Hz}$ ; $T_J$ (initial) = $25^\circ\text{C}$		100	
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3 \text{ ms}$		41	$\text{A}^2\text{s}$
$di/dt$	Critical rate-of-rise of on-state current	$f = 60 \text{ Hz}; T_J = 125^\circ\text{C}$		100	$\text{A}/\mu\text{s}$
$I_{GM}$	Peak gate current	$T_J = 125^\circ\text{C}$		2	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^\circ\text{C}$		0.5	W
$T_{stg}$	Storage temperature range			-40 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range			-40 to 125	$^\circ\text{C}$

Note: xx = voltage

**Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified) – Sensitive SCRs**

Symbol	Test Conditions		Value		Unit
			Sxx08xS2	Sxx08xS3	
$I_{GT}$	$V_D = 6V$ $R_L = 100 \Omega$	MAX.	200	500	$\mu\text{A}$
$V_{GT}$		MAX.	0.8		V
dv/dt	$V_D = V_{DRM}$ ; $R_{GK} = 1k\Omega$ ; $T_J = 110^\circ\text{C}$	TYP.	8		V/ $\mu\text{s}$
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 k\Omega$ $T_J = 110^\circ\text{C}$	MIN.	0.2		V
$V_{GRM}$	$I_{GR} = 10\mu\text{A}$	MIN.	6		V
$I_H$	$I_T = 20\text{mA}$ (initial)	MAX.	6	8	mA
$t_q$	$I_T = 2\text{A}$ ; $t_p = 50\mu\text{s}$ ; dv/dt=5V/ $\mu\text{s}$ ; di/dt=-30A/ $\mu\text{s}$	MAX.	50	45	$\mu\text{s}$
$t_{gt}$	$I_G = 2 \times I_{GT}$ PW = 15 $\mu\text{s}$ $I_T = 12\text{A}$	TYP.	4	5	$\mu\text{s}$

Note: xx = voltage x = package

**Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified) – Standard SCRs**

Symbol	Test Conditions			Value	Unit
				Sxx08x	
$I_{GT}$	$V_D = 12V$ $R_L = 60 \Omega$		MAX.	15	mA
$V_{GT}$			MAX.	1.5	V
dv/dt	$V_D = V_{DRM}$ ; gate open; $T_J = 100^\circ\text{C}$	400V	MIN.	350	V/ $\mu\text{s}$
		600V		300	
		800V		250	
		1000V		100	
	$V_D = V_{DRM}$ ; gate open; $T_J = 125^\circ\text{C}$	400V		250	
		600V		225	
		800V		200	
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 k\Omega$ $T_J = 125^\circ\text{C}$		MIN.	0.2	V
$I_H$	$I_T = 200\text{mA}$ (initial)		MAX.	30	mA
$t_q$	$I_T = 2\text{A}$ ; $t_p = 50\mu\text{s}$ ; dv/dt=5V/ $\mu\text{s}$ ; di/dt=-30A/ $\mu\text{s}$		MAX.	35	$\mu\text{s}$
$t_{gt}$	$I_G = 2 \times I_{GT}$ PW = 15 $\mu\text{s}$ $I_T = 16\text{A}$		TYP.	2	$\mu\text{s}$

Note: xx = voltage x = package

**Static Characteristics**

Symbol	Test Conditions			Value	Unit	
$V_{TM}$	$I_T = 16\text{A}$ ; $t_p = 380 \mu\text{s}$			MAX.	1.6 V	
$I_{DRM} / I_{RRM}$	$V_{DRM} = V_{RRM}$	Sxx08xyy	$T_J = 25^\circ\text{C}$	400 - 600V	MAX.	5
			$T_J = 110^\circ\text{C}$	400 - 600V		250
		Sxx08x	$T_J = 25^\circ\text{C}$	400 - 800V		10
				1000V		20
			$T_J = 100^\circ\text{C}$	400 - 800V		200
				1000V		3000
			$T_J = 125^\circ\text{C}$	400 - 800V		500

Note: xx = voltage, x = package, yy = sensitivity

**Thermal Resistances**

Symbol	Parameter	Value	Unit	
$R_{\theta(J-C)}$	Junction to case (AC)	Sxx08RSy	1.8	°C/W
		Sxx08LSy	3.4	
		Sxx08VSy	2.1	
		Sxx08DSy	1.5	
		Sxx08R	1.8	
		Sxx08L	3.4	
		Sxx08V	2.0	
		Sxx08D	1.5	
$R_{\theta(J-A)}$	Junction to ambient	Sxx08RSy	40	°C/W
		Sxx08LSy	65	
		Sxx08VSy	85	
		Sxx08R	40	
		Sxx08L	50	
		Sxx08V	70	

Note: xx = voltage, y = sensitivity

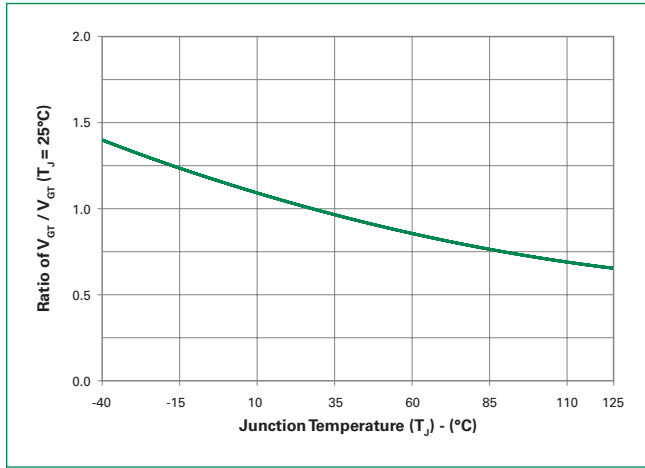
**Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature (Sensitive SCR)**



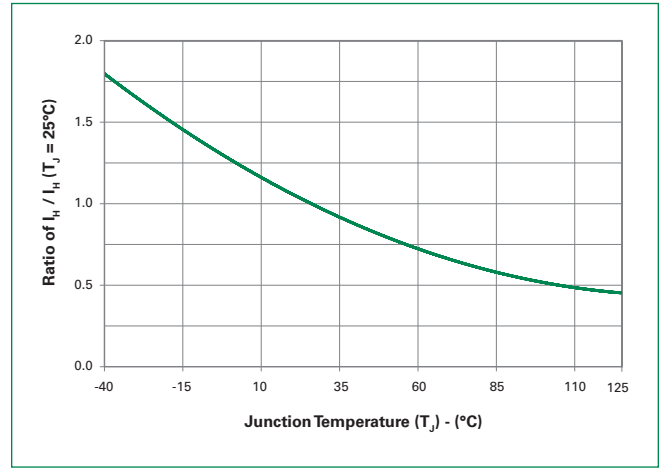
**Figure 2: Normalized DC Gate Trigger Current vs. Junction Temperature (Standard SCR)**



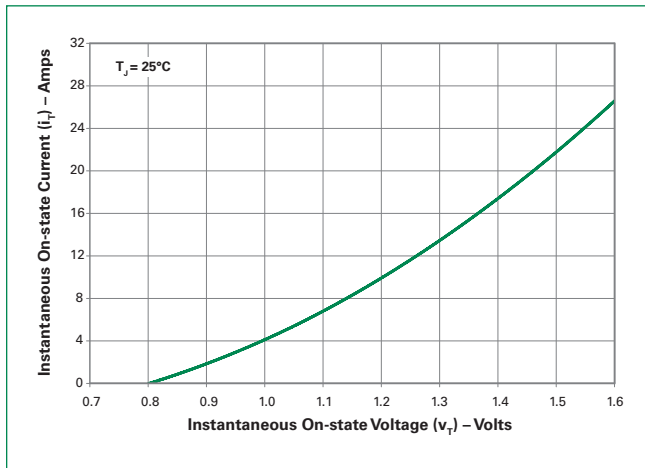
**Figure 3: Normalized DC Gate Trigger Voltage vs. Junction Temperature**



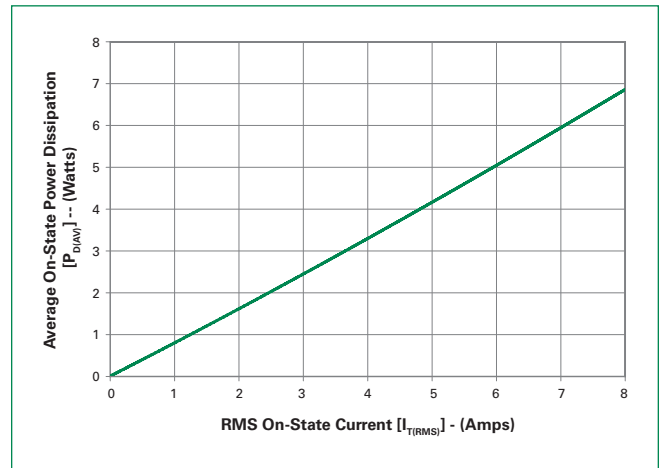
**Figure 4: Normalized DC Holding Current vs. Junction Temperature**



**Figure 5: On-State Current vs. On-State Voltage (Typical)**



**Figure 6: Power Dissipation (Typical) vs. RMS On-State Current**



**Figure 7: Maximum Allowable Case Temperature vs. RMS On-State Current**



**Figure 8: Maximum Allowable Case Temperature vs. Average On-State Current**



**Figure 9: Maximum Allowable Ambient Temperature vs. RMS On-State Current**



Note: xx = voltage, y = sensitivity

**Figure 10: Maximum Allowable Ambient Temperature vs. Average On-State Current**



**Figure 11: Peak Capacitor Discharge Current**



**Figure 12: Peak Capacitor Discharge Current Derating**



**Figure 13: Surge Peak On-State Current vs. Number of Cycles**



SUPPLY FREQUENCY: 60 Hz Sinusoidal  
 LOAD: Resistive  
 RMS On-State Current [ $I_{T(RMS)}$ ]: Maximum Rated Value at Specified Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

### Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp ( $T_L$ ) to peak)		5°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		5°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Temperature ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



### Physical Specifications

<b>Terminal Finish</b>	100% Matte Tin-plated
<b>Body Material</b>	UL recognized epoxy meeting flammability classification 94V-0
<b>Lead Material</b>	Copper Alloy

### Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

### Environmental Specifications

Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Thermal Shock</b>	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
<b>Autoclave</b>	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E

**Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead**



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

**Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab**



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22



**Dimensions — TO-251AA (V/I-Package) — V/I-PAK Through Hole**



Dimension	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.040	0.044	0.050	1.02	1.11	1.27
B	0.235	0.242	0.245	5.97	6.15	6.22
C	0.350	0.361	0.375	8.89	9.18	9.53
D	0.205	0.208	0.213	5.21	5.29	5.41
E	0.255	0.262	0.265	6.48	6.66	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
H	0.085	0.092	0.095	2.16	2.34	2.41
I	0.176	0.180	0.184	4.47	4.57	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.038	0.040	0.044	0.97	1.01	1.12
L	0.018	0.020	0.023	0.46	0.52	0.58
P	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11
R	0.034	0.039	0.044	0.86	1.00	1.11
S	0.074	0.079	0.084	1.86	2.00	2.11

**Dimensions — TO-252AA (D-Package) — D-PAK Surface Mount**



Dimension	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.040	0.043	0.050	1.02	1.09	1.27
B	0.235	0.243	0.245	5.97	6.16	6.22
C	0.106	0.108	0.113	2.69	2.74	2.87
D	0.205	0.208	0.213	5.21	5.29	5.41
E	0.255	0.262	0.265	6.48	6.65	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
H	0.085	0.092	0.095	2.16	2.33	2.41
I	0.176	0.179	0.184	4.47	4.55	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.038	0.040	0.044	0.97	1.02	1.12
L	0.018	0.020	0.023	0.46	0.51	0.58
M	0.000	0.000	0.004	0.00	0.00	0.10
N	0.021	0.026	0.027	0.53	0.67	0.69
O	0°	0°	5°	0°	0°	5°
P	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11

### Product Selector

Part Number	Voltage				Gate Sensitivity	Type	Package
	400V	600V	800V	1000V			
Sxx08RS2	X	X			0.2mA	Sensitive SCR	TO-220R
Sxx08LS2	X	X			0.2mA	Sensitive SCR	TO-220L
Sxx08VS2	X	X			0.2mA	Sensitive SCR	TO-251
Sxx08DS2	X	X			0.2mA	Sensitive SCR	TO-252
Sxx08RS3	X	X			0.5mA	Sensitive SCR	TO-220R
Sxx08LS3	X	X			0.5mA	Sensitive SCR	TO-220L
Sxx08VS3	X	X			0.5mA	Sensitive SCR	TO-251
Sxx08DS3	X	X			0.5mA	Sensitive SCR	TO-252
Sxx08R	X	X	X	X	15mA	Standard SCR	TO-220R
Sxx08L	X	X	X	X	15mA	Standard SCR	TO-220L
Sxx08V	X	X	X	X	15mA	Standard SCR	TO-251
Sxx08D	X	X	X	X	15mA	Standard SCR	TO-252

Note: xx = Voltage

### Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx08L/Ryy	Sxx08L/Ryy	2.2 g	Bulk	500
Sxx08L/RyyTP	Sxx08L/Ryy	2.2 g	Tube	500 (50 per tube)
Sxx08DyyTP	Sxx08Dyy	0.3 g	Tube	750 (75 per tube)
Sxx08DyyRP	Sxx08Dyy	0.3 g	Embossed Carrier	2500
Sxx08VyyTP	Sxx08Vyy	0.4 g	Tube	750 (75 per tube)
Sxx08L/R	Sxx08L/R	2.2 g	Bulk	500
Sxx08L/RTP	Sxx08L/R	2.2 g	Tube	500 (50 per tube)
Sxx08DTP	Sxx08D	0.3 g	Tube	750 (75 per tube)
Sxx08DRP	Sxx08D	0.3 g	Embossed Carrier	2500
Sxx08VTP	Sxx08V	0.4 g	Tube	750 (75 per tube)

Note: xx = Voltage; yy = Sensitivity

### TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



### Part Numbering System



### Part Marking System

TO-220 AB – (R Package)



TO-220 AB – (L Package)



TO-251AA – (V Package)  
TO-252AA – (D Package)





Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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